Early Analysis of Fault-Attack Effects for Cryptographic Hardware

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Overview

□ **Context(s) of fault effect analysis**

□ **Early analysis: methods and tools**

□ **Differences between paradigms: impact on tools and fault models**

□ **Conclusions and perspectives**

Evolution of

Fault Propagation Analysis Needs

Once upon a time … in space ...

- **Energetic particles (photons or charged particles) can affect the microelectronic devices and subsystems in several ways.**
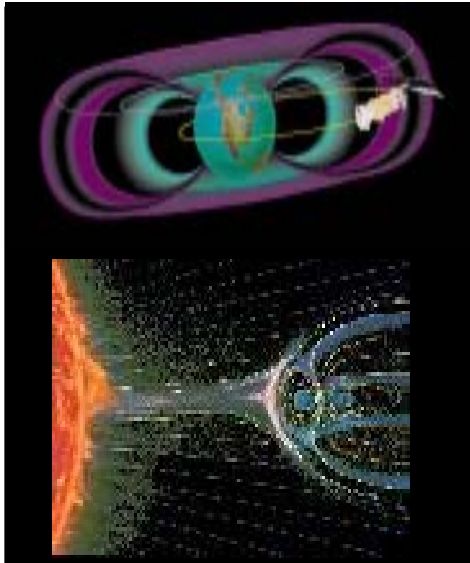
    - **Two main classes of effects:**

        - **Total Ionization Dose (TID): long-term degradation of electronics due to the cumulative deposited charge.**

        - **Single Event Effects (SEEs): occur when a single charged particle strikes the material, ionizes it and provokes a current pulse.**

    - **SEEs:**

        - **Single Event Latchups (SELs) create shorts between ground and power, and cause permanent functional damages (hard errors).**

        - **Single Event Upsets (SEUs) occur when a transient pulse provokes a bit flip in a device memory cell (soft errors).**

- **Radiation effect problems in space applications can be solved by:**

    - **using radiation hardened devices, by technology or design,**

    - **qualifying commercial circuits by radiation ground testing … and/or early analyses.**

Consequences of CMOS evolutions

- ☐ **CMOS shrinking**
  - ◆ **Reduced Vdd and noise margin**
  - ◆ **Reduced node capacitance**
  - ◆ **Increased frequency (increased probability of latching)**

- ☐ **Very deep sub-micron CMOS technologies are increasingly sensitive to the effects of alpha particles and atmospheric neutrons => SET / SEU / MBU.**

- ☐ **Studies focused on (but not limited to) SET/SEU-like faults**
  - ◆ **Can be extended to other faults (stuck-at, coupling, …), permanent or not**
  - ◆ **Partially covers noise problems (signal integrity)**

And also …

- ☐ **New security threats: fault attacks**
  - ◆ **Cryptography primitives: DES / RSA / AES …**
  - ◆ **Security locks (ratification counters, …)**
  - ◆ **…**

- ☐ **Various possibilities**
  - ◆ **Power glitch**
  - ◆ **Flash light**
  - ◆ **Laser**
  - ◆ **…**

- ☐ **Ultimately: logic fault(s)**

Organization

SECRET

Individual

Question ...

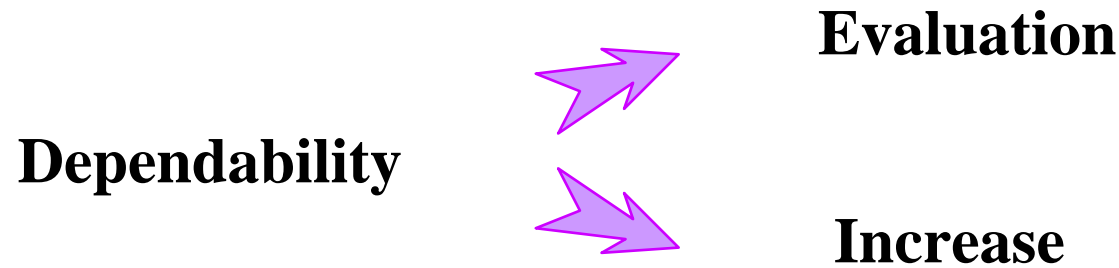There are "new" problem(s) with fault-based attacks …

… Are answers to "old" problems of some help ???

And up to what extent ?

Act II ...

Basics of

Existing Dependability Analysis Environments

Current goals of analysis environments

Evaluation

Dependability

Increase

- Working at various levels in the design flow
  (various design description levels),

- Automated,

- Compatible with classical up-to-date industrial design flows.

Link between analysis levels

Description level	Analysis	Qualitative info.	Quantitative info.
Behavioral/RTL	Behavioral simulation (emulation)	Error -> failure (application point of view)	P(failure|error)
Gate level (+ back annotation)	Gate level simulation (timed)	Glitch -> Error (latched) + refinement previous analysis	P(error|glitch)
Electrical/Physical	Electrical/Physical simulation	Particle or physical event -> glitch or bit-flip	P(glitch|particle) P(bit-flip|particle)

Estimation principle of application failure (limitations to be considered at high levels):

Critical logic paths

Environment

P(failure): P(failure|error) * [P(bit-flip|particle) + P(error|glitch) * P(glitch|particle)] * P(particle)

Critical nodes   **Sensitive nodes**   **Sensitive nodes**

Summary of the "early evaluation" goals

☐ **Develop injection methods and CAD environment to <u>early</u> analyze the <u>functional</u> impact of SEUs at the application level**

- ◆ **Early: performed on RTL descriptions (VHDL)**
- ◆ **Functional: technology independent (no detailed timing information – targets bit-flips, not transients in combinatorial logic network)**
- ◆ **Based on commercial tools and standard design flows**

☐ **Early identification of**

- ◆ **Functional failure modes (critical behaviors)**
- ◆ **Error propagation paths (critical nodes)**

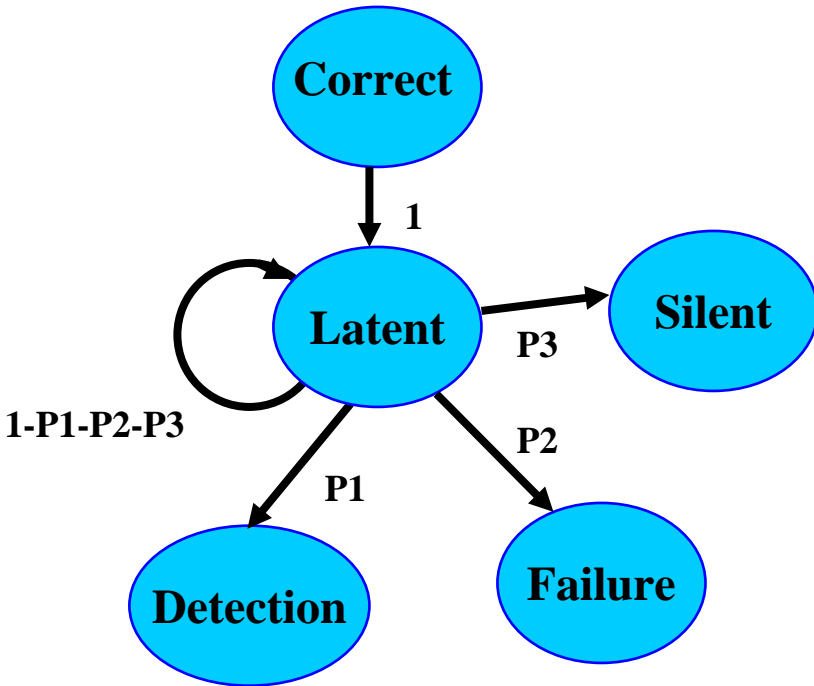**functional model, including qualitative and quantitative information**

☐ **Early assessment of**

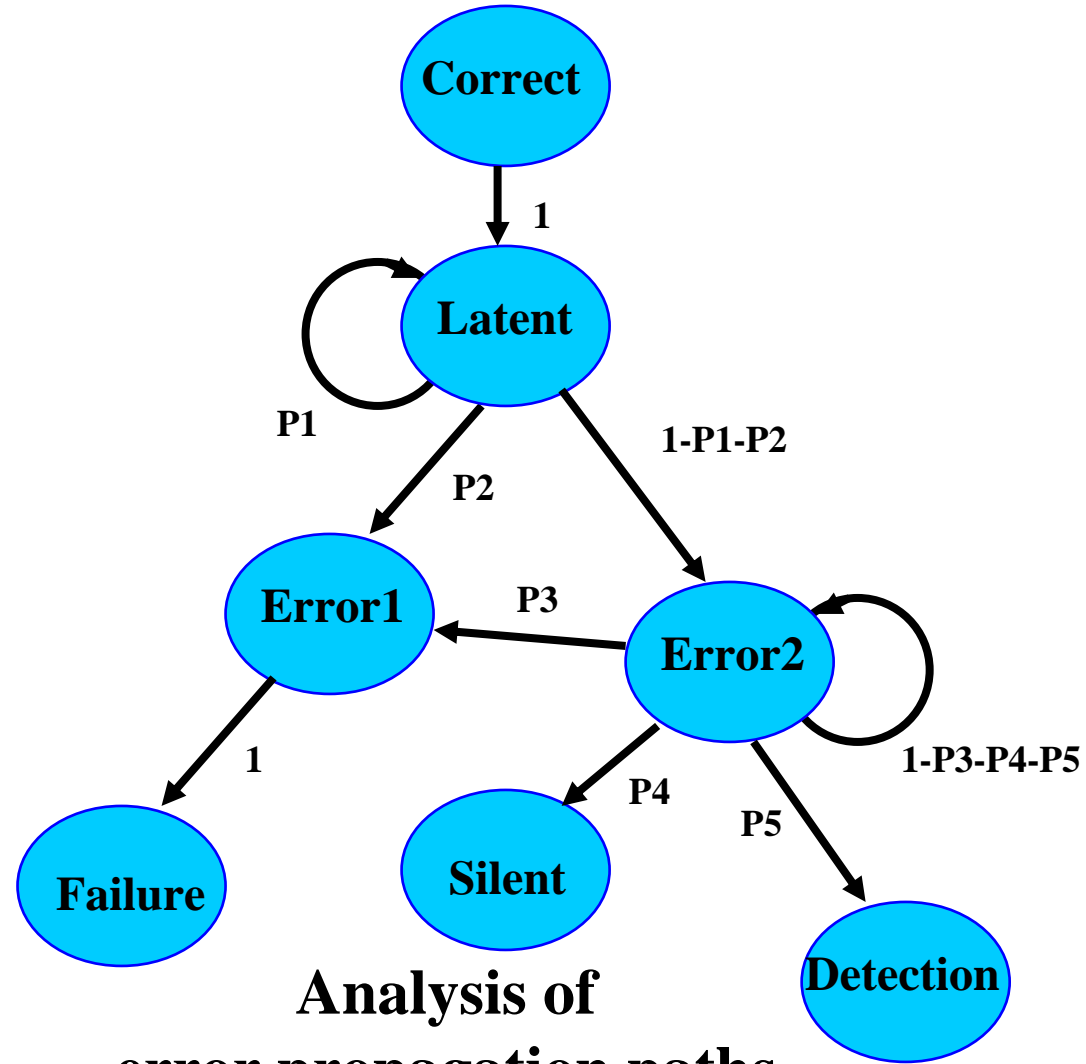- ◆ **Dependability level**
- ◆ **Design hardening efficiency**

Link with design hardening

Dependability analyses: alternative results
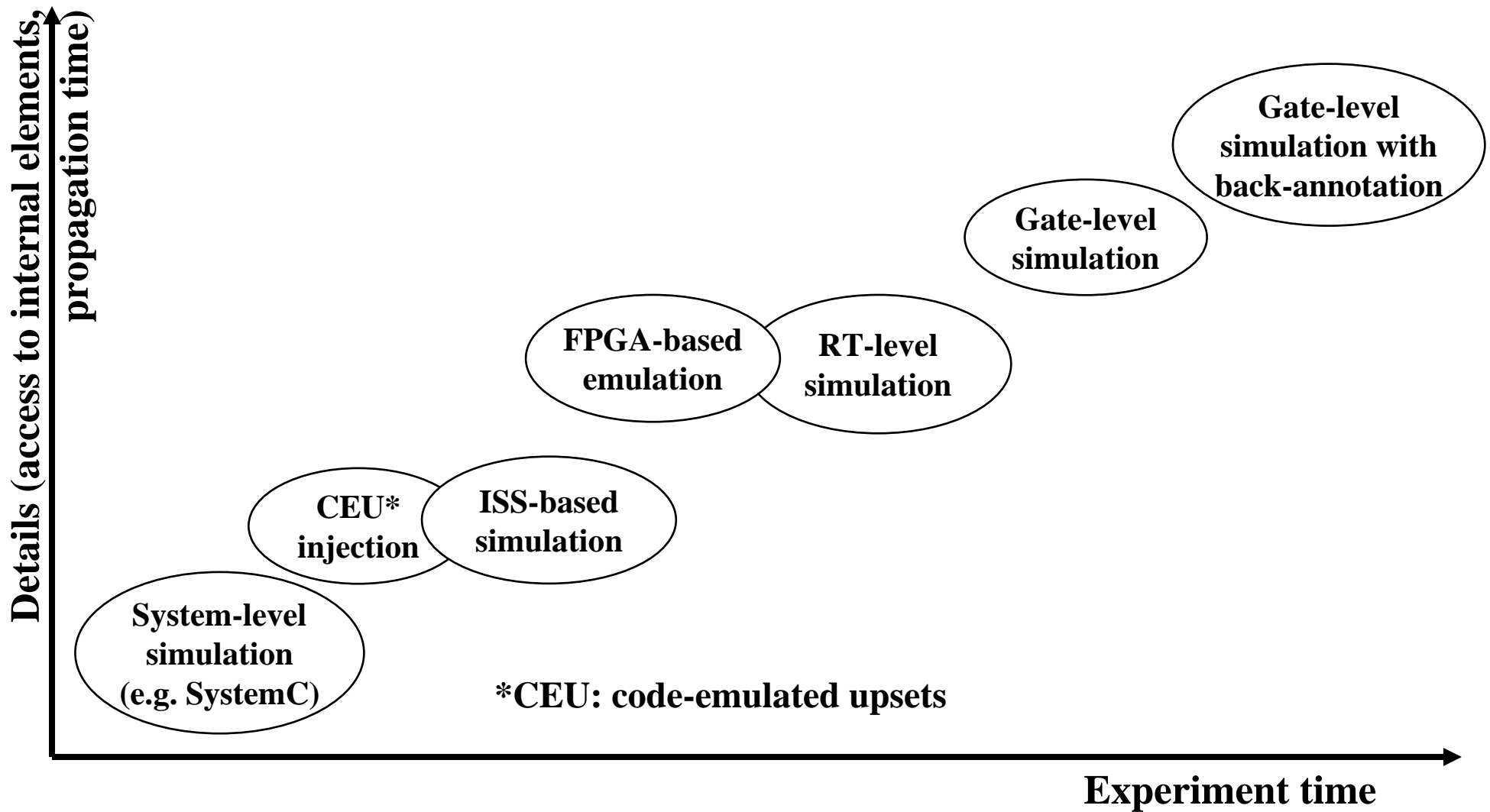
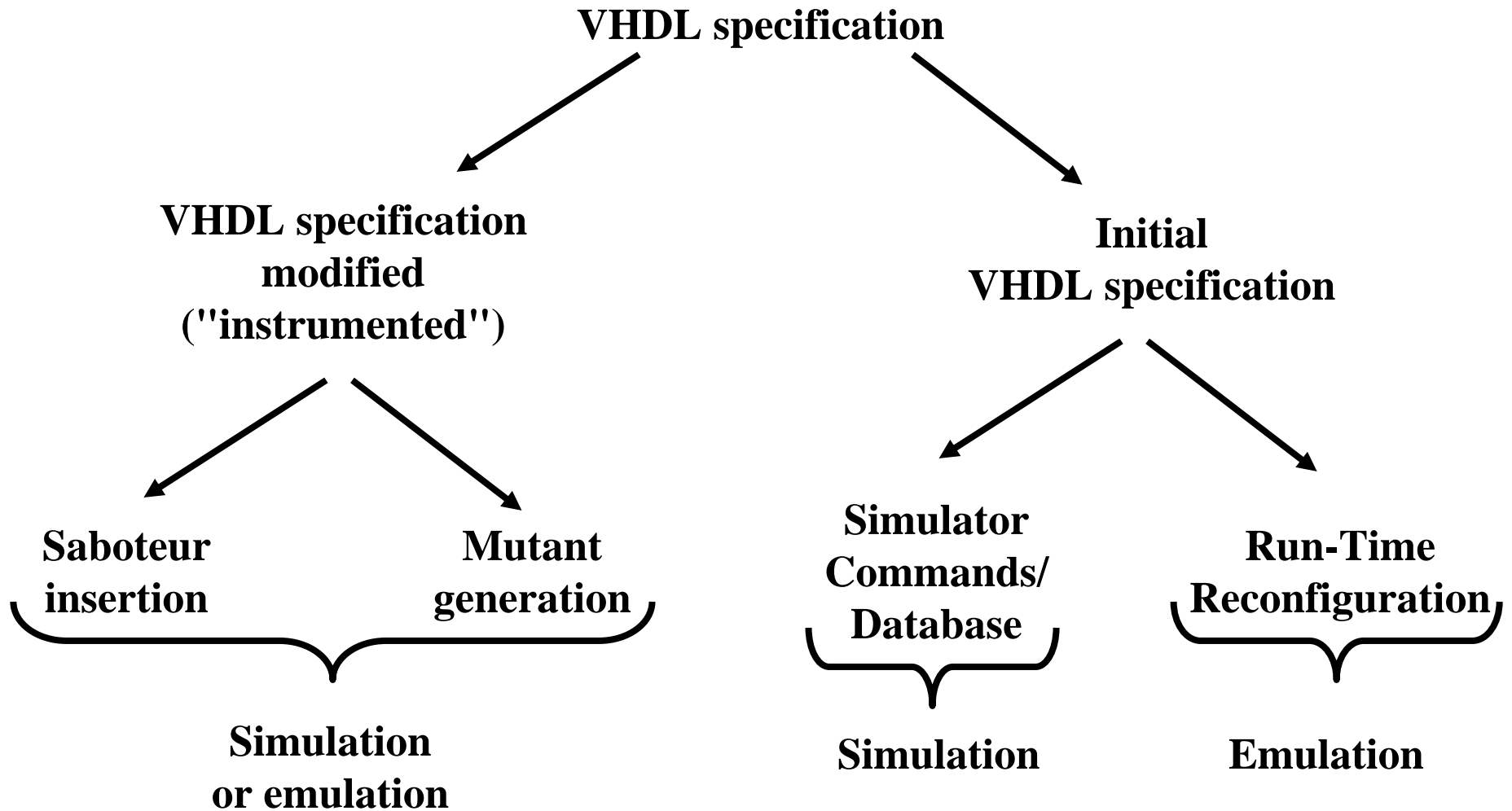**Cycle-by-cycle comparisons**

Fault classification

Analysis of error propagation paths

Alternative approaches

Details (access to internal elements, propagation time) — vertical axis

Experiment time — horizontal axis

- Gate-level simulation with back-annotation
- Gate-level simulation
- FPGA-based emulation
- RT-level simulation
- CEU* injection
- ISS-based simulation
- System-level simulation (e.g. SystemC)

*CEU: code-emulated upsets

Alternatives for fault injection campaigns

VHDL specification

VHDL specification modified ("instrumented")

Initial VHDL specification

Saboteur insertion

Mutant generation

Simulator Commands/ Database

Run-Time Reconfiguration

Simulation or emulation

Simulation

Emulation

Analysis flow: overview

Functional failure mode analysis of a digital integrated circuit

User Specification

- Hierarchical VHDL (synthesizable)
- Campaign definition
- Input vectors (workload)

Injection campaign
=> **VHDL simulation**
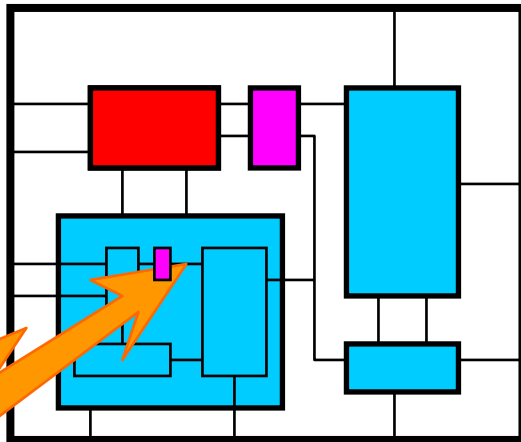=> **Hardware prototyping (FPGA)**

Data analysis
=> **Reached states**
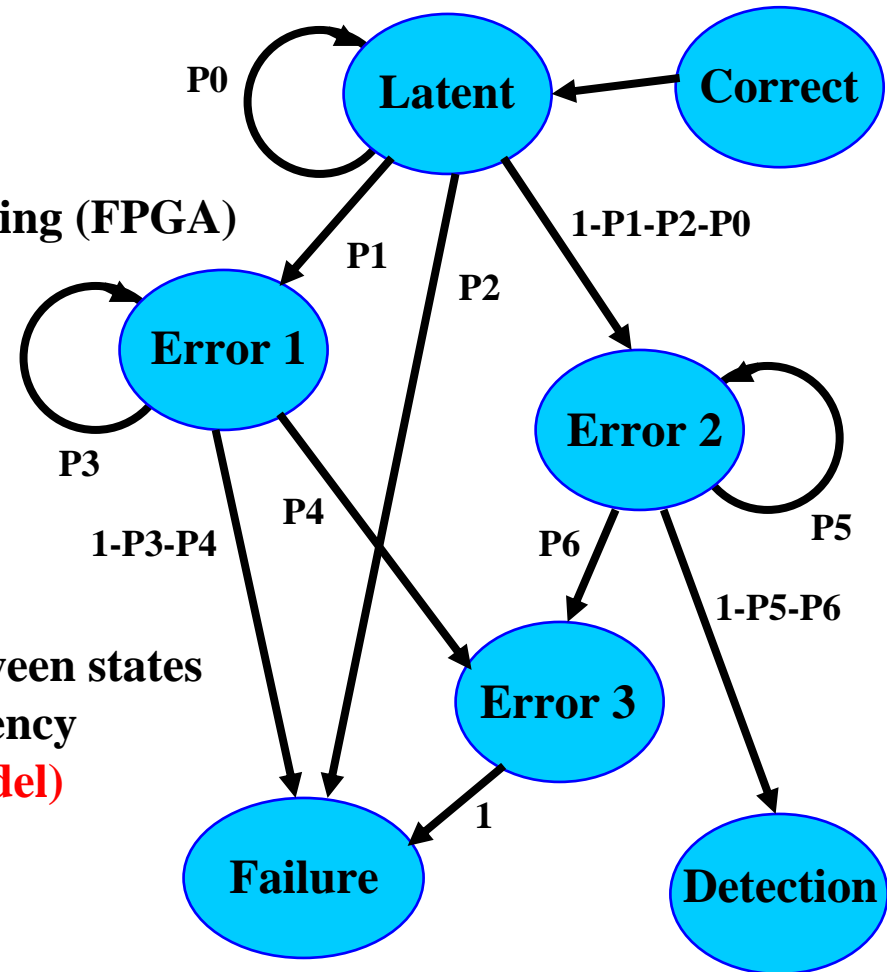=> **Transitions between states**
=> **Probability / latency**
(no pre-defined model)

Fault/error model + target
=> **saboteurs**, **mutants**

Latent
P0
Correct
1-P1-P2-P0
P1
P2
Error 1
P3
Error 2
P5
1-P3-P4
P4
P6
1-P5-P6
Error 3
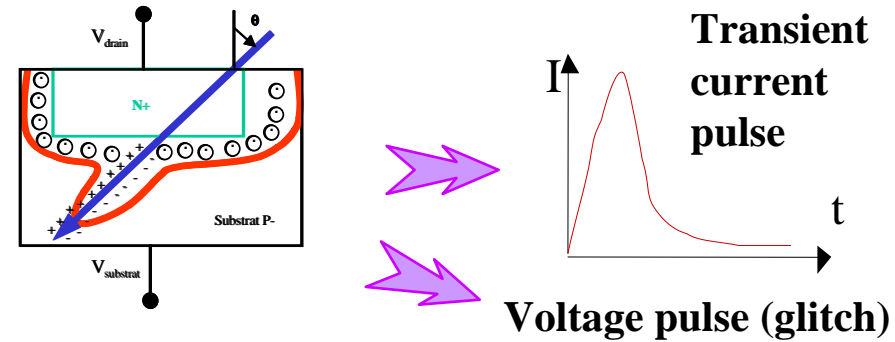1
Failure
Detection

Controlled generation of mutants

☐ **"Controlled generation" of mutants implies:**

◆ **Generation from high-level (RT-level) descriptions**

(available early in the design process)

◆ **Significant faulty behaviors**

(related to actual fault effects observable in the field => SEUs)

◆ **Optimization for synthesis (compatibility with simulation and emulation)**

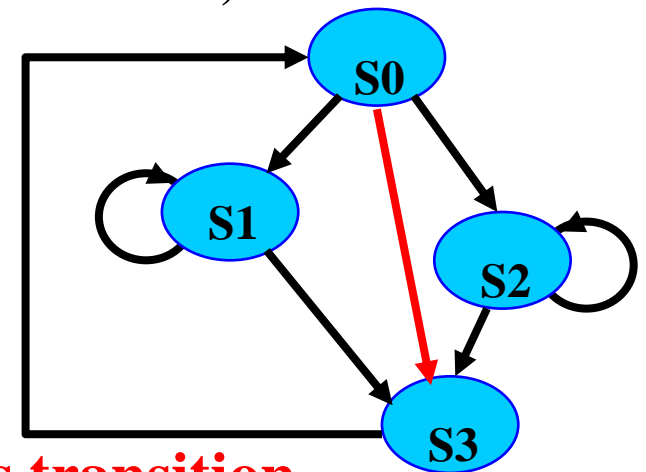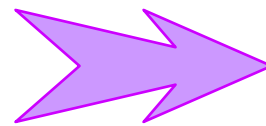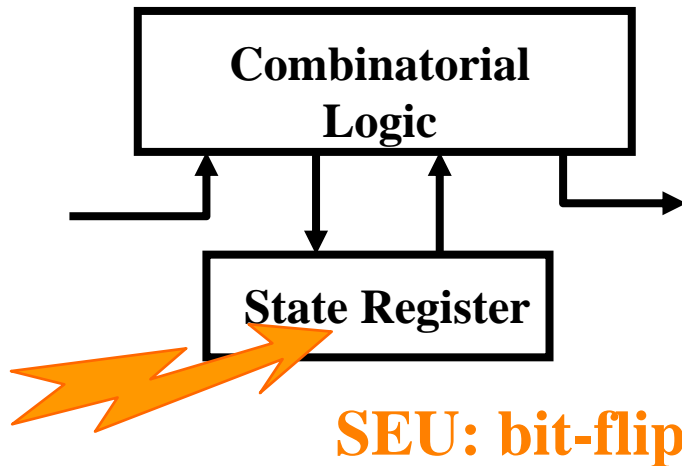◆ **Taking into account the limitations of hardware emulation systems**

☐ **Criteria for quality evaluation:**

◆ **Number of additional I/Os (number of sub-campaigns)**

◆ **Number of gates after synthesis (emulation hardware complexity)**

◆ **Maximum frequency (time required for the injection campaign)**

Levels of fault/error injection for SEUs

☐ **Physical level: a single charged particle incident on the IC generates a dense track of electron hole pairs and this ionization causes a transient.**

V_{drain}

N+

Substrat P-

$V_{substrat}$
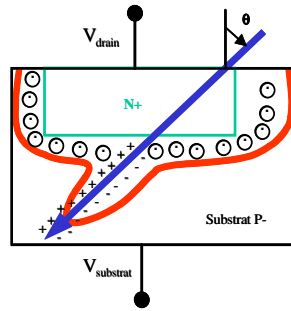
Transient current pulse

I

t

Voltage pulse (glitch)

☐ **High-level injection (RT-level control flowcharts, or FSMs – state registers), with or without knowledge on the state assignment (can be easily refined when the actual state codes are known):**
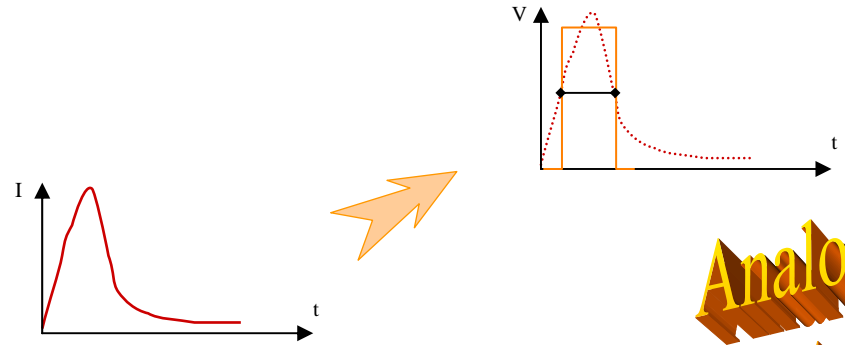
Combinatorial Logic

State Register

SEU: bit-flip

S0
S1
S2
S3

Erroneous transition
(between existing states)

Targeted faults

Modeling levels of a SEU

Physical
(electron/hole pairs)
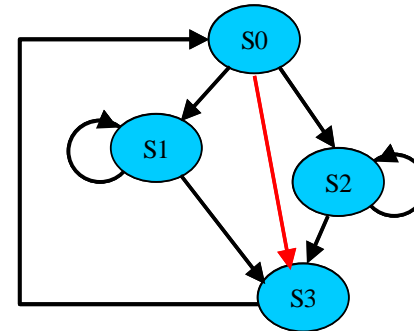
Electrical
(current or voltage pulse)

Analog parts

Logic
(bit-flip, signal glitch)

Behavioral
(e.g. erroneous transition)

Digital parts

Adequate for

Security-related Fault Injections ?

Which aspect ?

☐ **Circuit/application modeling ?**

◆ **Similar …**

◆ **Main difference between security and safety assessment: protections sized according to the potential losses (and attack investments)**

☐ **Definition of failure types ?**

◆ **Up to the user ! (conditions on signals)**

☐ **Type of faults to be injected during the experiments ?**

◆ **… Here is the gap!**

Fault modeling: paradigms

- **(Off-line) Test paradigm**
  - ◆ **Defects : manufacturing, aging**
  - ◆ **Permanent / intermittent faults**

- **(On-line) Test paradigm**
  - ◆ **Faults induced by the environment (or signal integrity)**
  - ◆ **Transient (or intermittent) faults**
  - ◆ **Low occurrence probability**
  - ◆ **High locality (example : particle)**

- **Security paradigm (attacks)**
  - ◆ **Faults induced intentionally (hackers)**
  - ◆ **Transient (or intermittent) faults**
  - ◆ **High occurrence probability (induced intentionally)**
  - ◆ **Variable locality (example : flash light vs. focused laser beam)**

Selection of fault models

□ **Gate-level (or upper) modeling, <u>non-intrusive</u> (or semi-intrusive) attacks (no circuit modification)**

□ **Four basic models**

- ◆ **Stuck-at (single / multiple - transient)**
- ◆ **Delay faults**
- ◆ **SET (transient inversion of signals)**

- ◆ **SEU / MBU => memory elements**

□ **Delay faults, SETs: require gate-level knowledge (propagation time)**
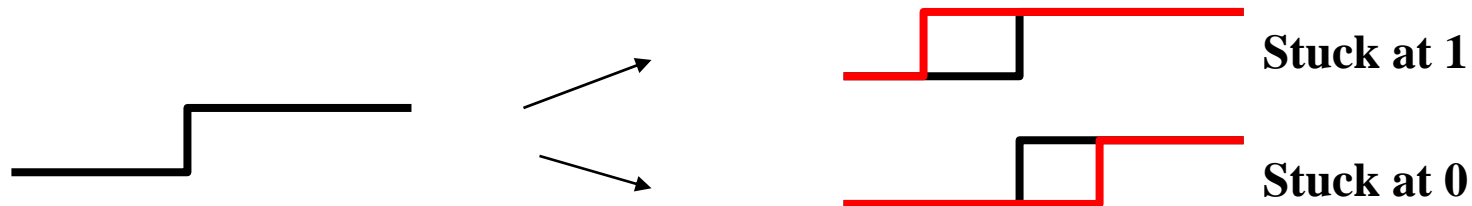
□ **Stuck-ats: can be applied at RT-level on selected targets**

Comparison of models (1)

- ☐ **Stuck-at**
  - ◆ **Polarity to be defined: zero or one**
  - ◆ **Transient in the security paradigm**
  - ◆ **Can be applied at gate level, or at RT level (on selected nodes)**

- ☐ **Delay faults (positive or negative)**
  - ◆ **Can be applied only at gate level, mainly after P&R**
  - ◆ **Can be modeled as stuck-ats with the required polarity and a duration equal to the delay, occurring or disappearing when the event occurs on the target signal**

Stuck at 1

Stuck at 0

Comparison of models (2)

□ **SET**

◆ Can be applied only at gate level, mainly after P&R

◆ Several definitions … Usually, forced inversion on a node (without taking into account events that should occur during the fault duration)
=> equivalent to a transient stuck-at … on a given polarity

◆ Duration generally assumed inferior to the clock period

□ **SEU/MBU**

◆ Direct bit-flip in a memory element (direct error, without activation and propagation of a fault)

◆ Can be applied at gate or RT level

◆ Few common points with the other models

Comparison of models (3)

□ **Conclusion: 2 models can be sufficient**

◆ **SEU/MBU**

◆ **Transient stuck-ats, with duration D**

  – **D being potentially superior to the clock period (generalization of SETs => multi-cycle faults)**

  – **Analysis including all possible occurrence instants at gate level (to include all delay faults)**

  – **At RT-level, duration defined by a number of clock cycles (functional analysis) + selection of significant targets**

[DURACELL project]

Attributes

- **High number of possible attributes (or parameters)**
  - ◆ Specify the characteristics and the selection of faults and targets for a given model
  - ◆ General framework of the study: logic level, transient faults, … => limitation of the list of attributes

- **Main attributes in the studied context:**
  - ◆ Duration of faults (if stuck-at)
  - ◆ Spatial and temporal multiplicity
  - ◆ Correlation of multiple faults (spatial or temporal)
  - ◆ Target and injection time selection (exhaustive/deterministic/random)
  - ◆ Type of random distributions (uniform, gaussian, …)
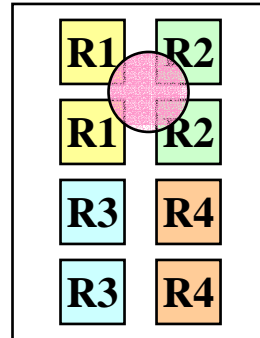
- **Intervals of values: depend on context/technology**
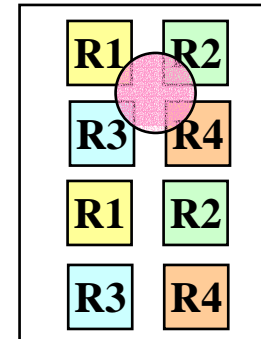
Definition of attributes: example

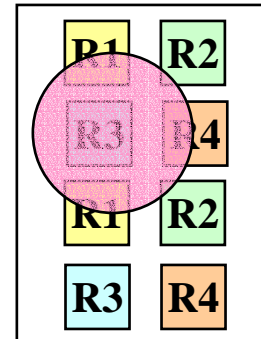- **Spatial multiplicity (MBU) – laser attack**
- **Depends on**
  - ◆ **Laser focus**
  - ◆ **Placement/routing**
  - ◆ **Cell sensitivity**
  - ◆ **…**

P&R-1, focus 1
=> mult. up to
2 per element,
4 elements

P&R-2, focus 1
=> mult. up to
1 per element,
4 elements

P&R-2, focus 2
=> mult. up to
2 per element,
4 elements

- **High-level analysis: no information on P&R**
  => assumptions / limitations (e.g. limited to the elements in a
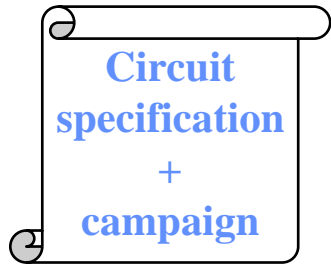 **given register), but gives constraints on P&R for coherence**

Conclusions

- **Suitable analyses for fault-based attacks are not so different from previous concerns …**

- **… and existing analysis environments and methodologies can be used in this (new) context …**

- **BUT fault models must be revisited …**

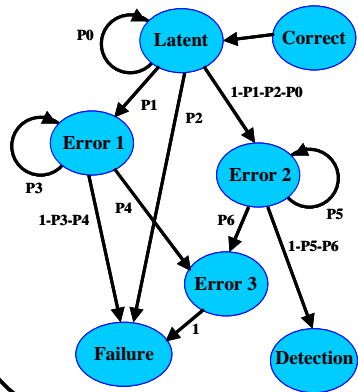- **… and tools must be extended (e.g. generation of new types of mutants).**

Perspective: future view

Dependability analysis/Characterization

- **Functional analysis**
- **Multi-level fault injection**
- **Behavioral model generation**
- **Anticipation of radiation ground testing**

Circuit specification + campaign

Injection: saboteurs/mutants

P0

Latent — **Correct**

1-P1-P2-P0

P1

P2

Error 1

Error 2

P3

P4

P5

1-P3-P4

P6

1-P5-P6

Error 3

1

Failure

Detection

Campaign: simulation/emulation + data analysis
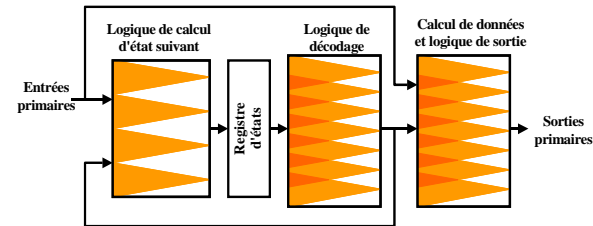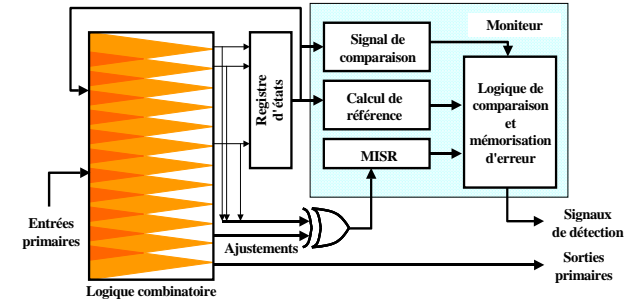
Hardening

+ configurable IPs

Sequencing error detection

Validation

Fault tolerance / On-line testing

- **Source-to-source transformations of synthetizable RTL descriptions**
- **Architectures with limited redundancy**

Moniteur

Signal de comparaison

Registre d'états

Calcul de référence

Logique de comparaison et mémorisation d'erreur

MISR

Entrées primaires

Ajustements

Logique combinatoire

Signaux de détection

Sorties primaires

Logique de calcul d'état suivant

Logique de décodage

Calcul de données et logique de sortie

Entrées primaires

Registre d'états

Sorties primaires

SEU tolerance

- **Efficient implementation/perenniality**
- **Earlier validation of the dependability properties (circuit and system level)**